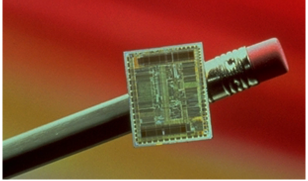

ICS904/CD2IC : Cell Design For Digital Integrated Circuits

The bases of CMOS digital circuits. . .

Yves MATHIEU

yves.mathieu@telecom-paristech.fr

Outline

Introduction

CMOS technology

bases of CMOS logic

CMOS logic efficiency

Moore’s laws

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Building a logic gate

What do we need ?

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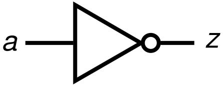

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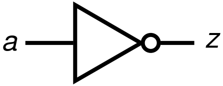

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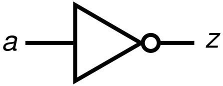

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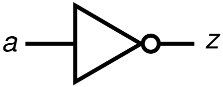

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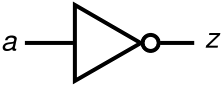

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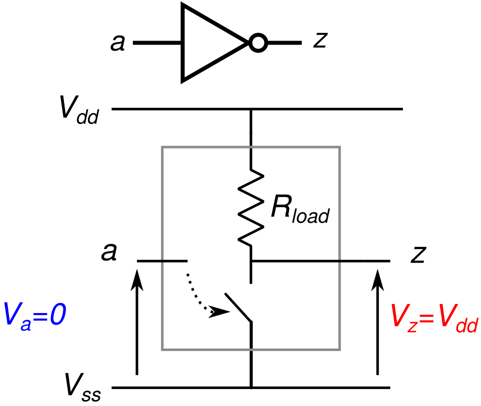

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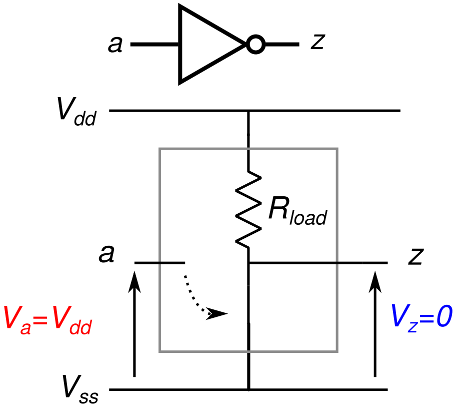
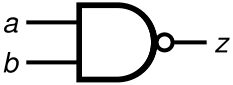
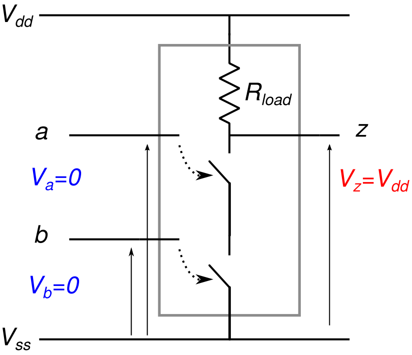


Let's try to build a more complex gate . . .

The two input NAND gate





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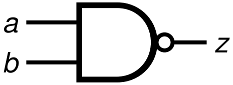

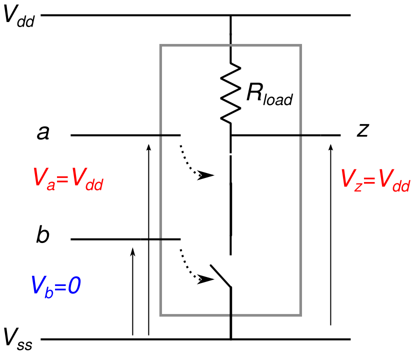

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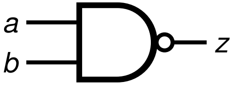

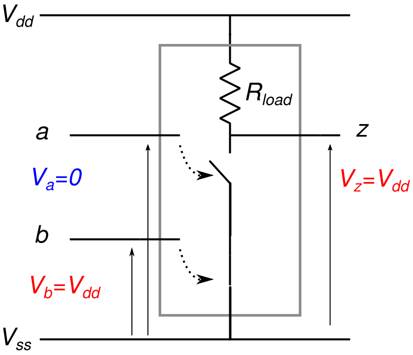

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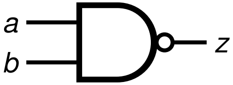

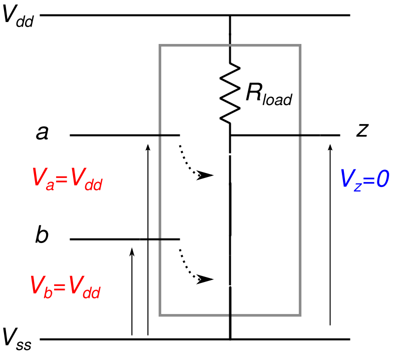

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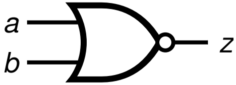

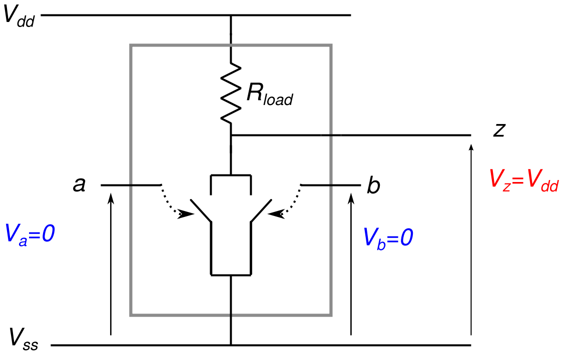

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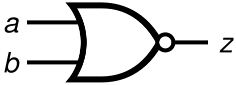

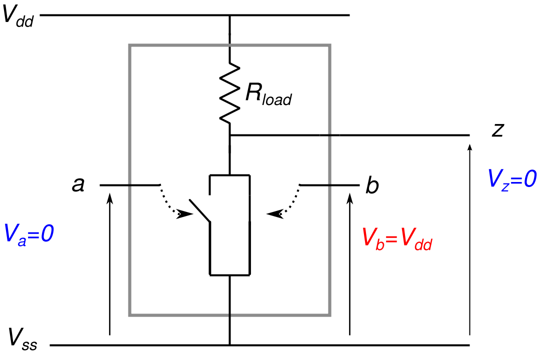

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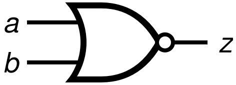

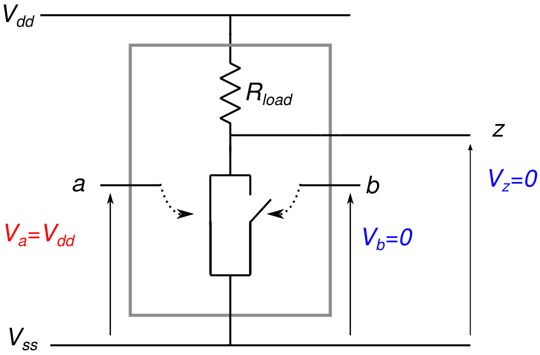

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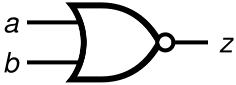

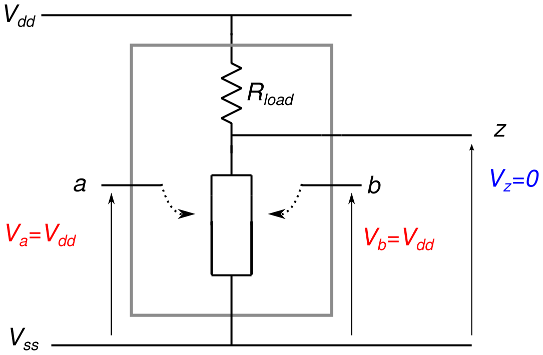

Very simple structures

but. . .

- A permanent current flows through the gate when the logic output is **0** :
  - The only usefull power consumption should be linked to the **activity** of gates not to their state. . .
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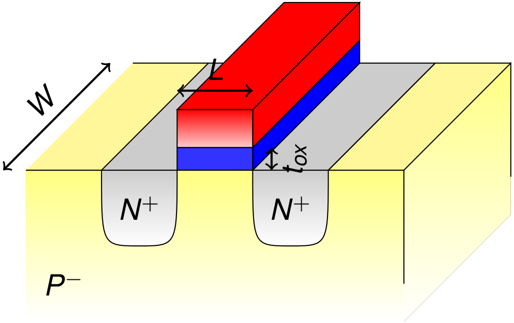
bases of CMOS logic

CMOS logic efficiency

Moore’s laws

The MOS transistor

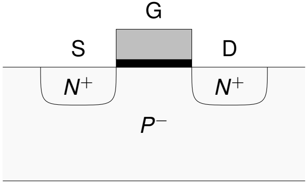
Metal Oxide Semiconductor



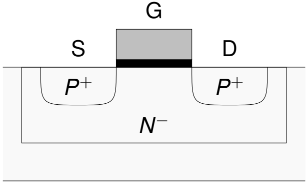
CMOS transistors

Complementary Metal Oxide Semiconductor

- Gate : G, Drain : D, Source : S, Threshold Voltage : V_T
- With $V_{TN} > 0$ and $V_{TP} < 0$



nMOS transistor



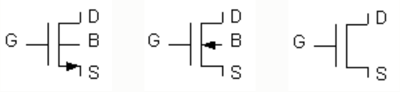
pMOS transistor

- N channel
- Electrons current
- Conduction if $V_{gs} > V_{TN}$

- P channel
- Holes current
- Conduction if $V_{gs} < V_{TP}$

Simplistic model of the NMOS transistor

Schematic Symbols



Cut-off region

$$\text{If } V_{GS} \leq V_{TN} \text{ then } I_{DS} = 0$$

Conduction region (Saturation region)

$$\text{If } V_{GS} > V_{TN} \text{ then } I_{DS_{max}} = K_n \cdot (V_{GS} - V_{TN})^2$$

Technological and geometrical factors

$$K_n = \frac{1}{2}\mu_{0N} \cdot C'_{ox}\frac{W_N}{L_N}$$

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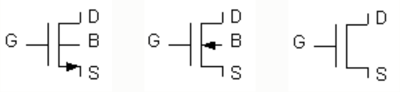

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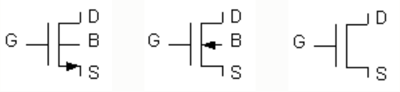

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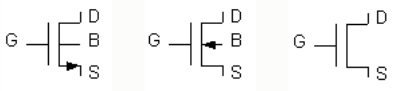

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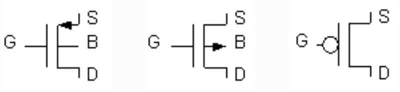

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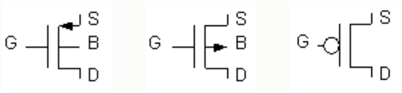

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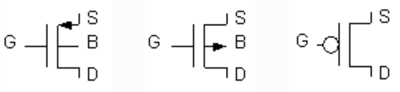

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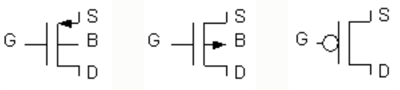

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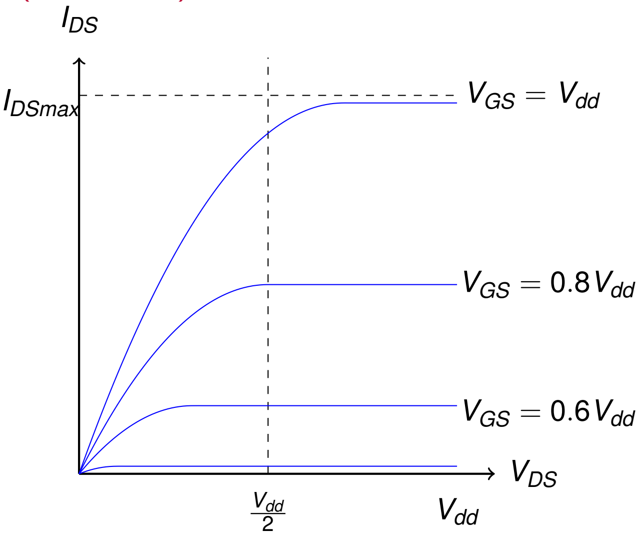
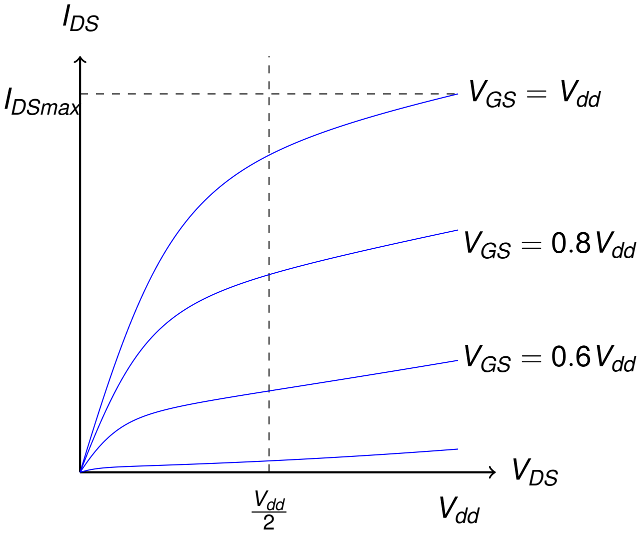
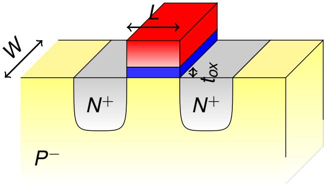
$I_{DS} = f(V_{GS}, V_{DS})$



28nm node. NMOS transistor



T_{ox} : gate oxide thickness



$C_{ox} = 1.15fF$

$R_{dsON} = 510.00\Omega$

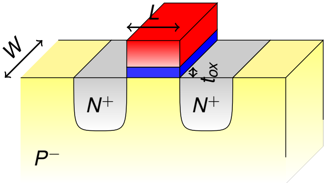
$I_{dsmax} = 880.00\mu A$

$L = 65.00nm$

$W = 1000.00nm$

$t_{ox} = 1.30nm$

L : Gate Length



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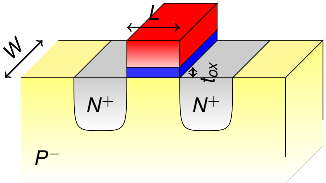

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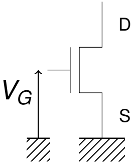
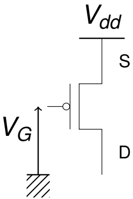
MOS transistors and logic levels

Two non ideal electronic switches



nMOS Transistor with Source connected to Ground.

- $V_G = V_{ss}$
  $\Rightarrow$ open switch
- $V_G = V_{dd}$
  $\Rightarrow$ closed switch



pMOS Transistor with Source connected to power supply

- $V_G = V_{ss}$
  $\Rightarrow$ closed switch
- $V_G = V_{dd}$
  $\Rightarrow$ open switch

CMOS logic

CMOS invertor

- Boolean input value $a = 0$
  - → $V_a = 0$
    - → nMOS cutoff
    - → pMOS conducting
  - → $V_z = V_{dd}$

→ boolean output value $z = 1$

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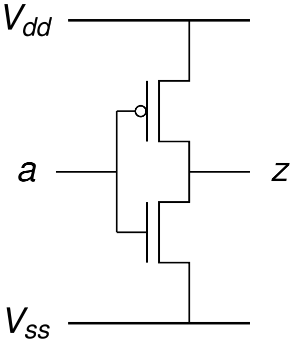
→ Boolean output value $z = 0$

No static power consumption (first order approximation)



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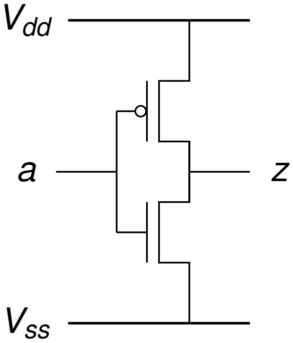
- boolean input value $a = 1$
  - → $V_a = V_{dd}$
    - → nMOS conducting
    - → pMOS cutoff
  - → $V_z = 0$

→ Boolean output value $z = 0$

No static power consumption (first order approximation)



CMOS logic

CMOS invertor

- Boolean input value $a = 0$
  - → $V_a = 0$
    - → nMOS cutoff
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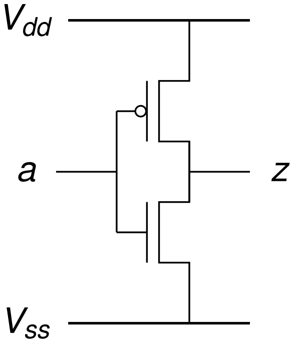

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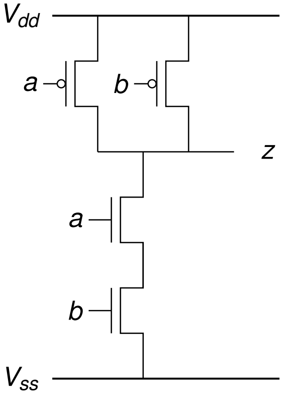
CMOS logic

The two input NAND gate



Outline

Introduction

CMOS technology

bases of CMOS logic

CMOS logic efficiency

Moore's laws

Performance criterions

- **Area/cost** :
  The smaller the chip is, the better the efficiency of production and therefore the lower the manufacturing cost.
  - Using smaller transistors (technology evolution)
  - Using less transistors (architectural choices)
- **Speed** :
  Faster logic gates implies larger processing power.
  - How to increase the clock frequency ?
- -> **Power consumption** :
  Computation means power consumption.
  - How to minimize this power consumption ? (Internet Of Things) . . .)
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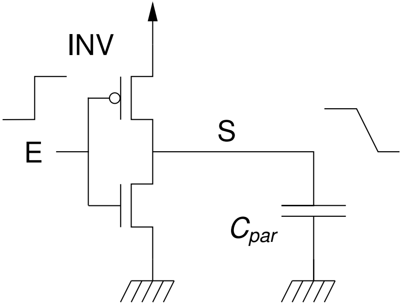
Computation time of a logic gate

The simple case of a rising edge at the input of an invertor

- Hypothesis 1 : The rising edge has a null duration.
- Hypothesis 2 : The only parasitic capacitance taken into account is the gate capacitance.
- Hypothesis 3 : The current flowing through the transistors for charge or discharge of parasitic capacitance C_{par} is roughly equal to $I_{DS_{max}}$



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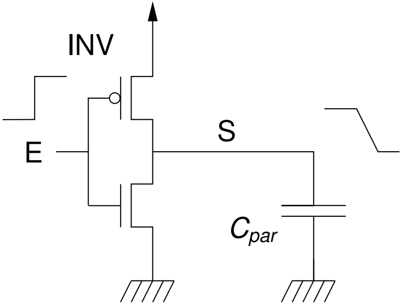

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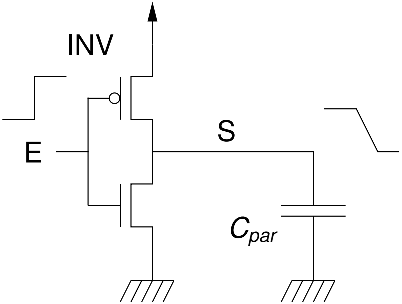
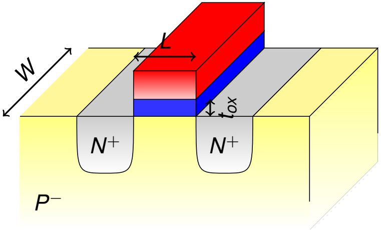


Computation time of a logic gate

MOS transistor



Current through the conducting transistor

$$I_{DS_{max}} = K_n \cdot (V_{dd} - V_{TN})^2 \text{ with } K_n = \frac{1}{2}\mu_{0N} \cdot C'_{ox}\frac{W_N}{L_N}$$

Parasitic capacitance of the transistor gate

$$C_{ox} = C'_{ox} W_N \cdot L_N$$

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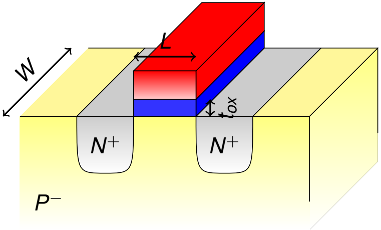

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Computation time of a logic gate

Computation time of an invertor

Current equation for the parasitic capacitance

$$I_{C_{par}} = C_{par} dV_{C_{par}} / dt$$

The NMOS transistor acts as a current source

$$I_{C_{par}} \approx I_{DSmax} = K_n \cdot (V_{dd} - V_{tn})^2$$

Discharge from V_{dd} to 0

$$t_{comp} = C_{par} \frac{\Delta V}{I_{DSmax}} = C_{par} \frac{V_{dd}}{K_n \cdot (V_{dd} - V_{tn})^2}$$

Encreasing the power-supply voltage in order to increase speed (overclocking) ? (bad way)

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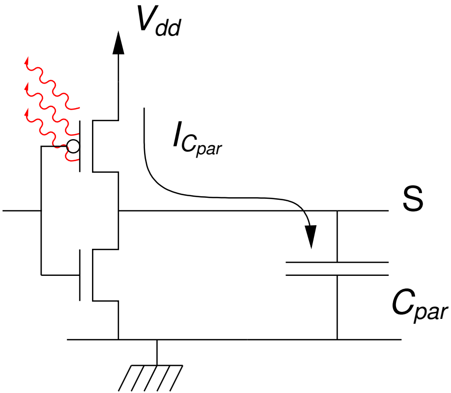
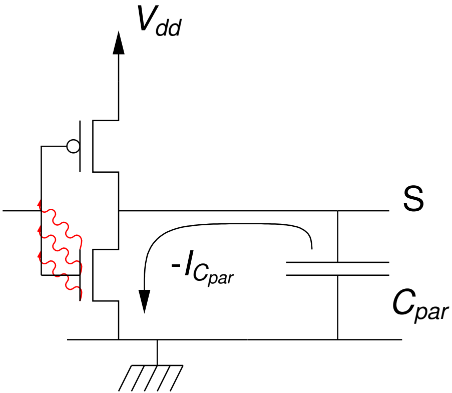
Power consumption of CMOS logic

Dissipated energy versus stored energy



Rising edge



Falling edge

Power consumption of CMOS logic

Energy balance

Charging : Energy comes from the power supply

$$E_{V_{dd}} = C_{par} \int_0^{V_{dd}} V_{dd}\, \mathrm{d}V_s = C_{par}\, {V_{dd}}^2$$

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Power consumption of CMOS logic

Power consumption of a full chip

- Let C_{chip} be the overall parasitic capacitance of the chip.
- Let F_{clk} be the operating frequency of the chip clock (synchronous logic)
- Let T_{act} (activity) be the mean transition probability of signals during a single cycle of the clock ($T_{act} \approx 0.3$)

Overall power consumption of the chip

$$P_{circuit} \approx T_{act} F_{clk} C_{chip} {V_{dd}}^2$$

What do you think now of overclocking ?

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Moore’s laws

A bit of history

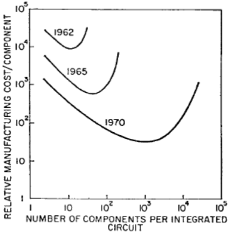
Moore’s "law(s)"

Intel 1969 - 106 employees (2015 - 80000 employees)

https://commons.wikimedia.org/wiki/File:Intel_Mountain_View_in_1969.jpg

A bit of history

Moore’s "law(s)"



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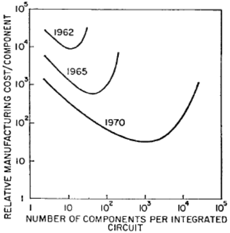

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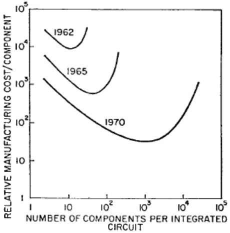

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Moore’s "law(s)"

- This empirical observation became a prediction.
- This prediction became a roadmap for silicon foundries.
  - Research and development expenditure adjustment. . .
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- Moore’law widened to other key parameters :

  Processing power of . . . double every . . . years

  Power consumption of . . . is divided by two every . . . years

Moore’s laws were exponential laws, followed during more than four decades.

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Technology evolution model

"Theoritical downsizing"

- Technology "nodes" :
  - A technology node is defined by the minimum gate length of the transistor (90nm, 65nm, 40nm, 28nm, . . .)
  - For each new node silicon founders try to reduce the transistor area with a factor of **2**
  - *Foundries* are investing billions of dollars in order to follow this objective . . .
- A linear reduction factor of $\beta = \sqrt{2}$ is used :
  - The width W and the length L of transistors are divided by β.
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Theoritical downsizing

Performance evolutions

Parasitic capacitances as a function of β

$$C_{par}(\beta) = (W/\beta)(L/\beta)(\beta C'_{ox}) = \frac{C_{par}}{\beta}$$

Energy consumption of a gate as a function of β

$$E_{gate}(\beta) = \frac{C_{par}}{\beta}(\frac{V_{dd}}{\beta})^2 = \frac{E_{gate}}{\beta^3}$$

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Reducing costs and power consumption

- Keeping the clock frequency constant.
  - $F_{clk}(\beta) = F_{clk}$
- The area reduction implies a price reduction
  - $Area(\beta) = \frac{Area}{\beta^2}$
- Power consumption is lower.
  - $P_{chip}(\beta) = T_{act} F_{clk} \frac{E_{chip}}{\beta^3} = \frac{P_{chip}}{\beta^3}$
- This strategy is particularly interesting for mobile systems :
  - Transition from high-end devices to low-end devices (smartphones),
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Theoritical downsizing

Reducing costs and power consumption

- Keeping the clock frequency constant.
  - $F_{clk}(\beta) = F_{clk}$
- The area reduction implies a price reduction
  - $Area(\beta) = \frac{Area}{\beta^2}$
- Power consumption is lower.
  - $P_{chip}(\beta) = T_{act} F_{clk} \frac{E_{chip}}{\beta^3} = \frac{P_{chip}}{\beta^3}$
- This strategy is particularly interesting for mobile systems :
  - Transition from high-end devices to low-end devices (smartphones),
  - New usages for ultra-low power devices (Internet Of Thinks).

Theoritical downsizing

Enhancing computational power

- Using maximum achievable frequency
  - $F_{clk}(\beta) = \beta F_{clk}$
- Using maximum achievable complexity (more transistors with the same area)
  - $Area(\beta) = Area$
- Power consumption doesn't change
  - $P_{chip}(\beta) = P_{chip}$
- This strategy is usefull for server CPUs.
  - Computational power is enhanced using higher frequencies.
  - Computational power is enhanced using parallelism.

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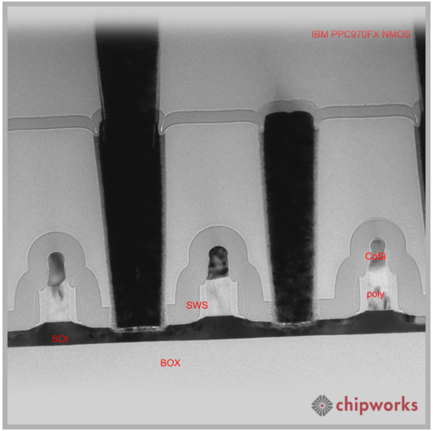
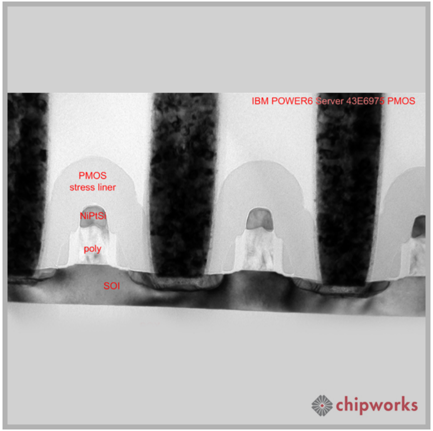
MOS Transistor : 2004



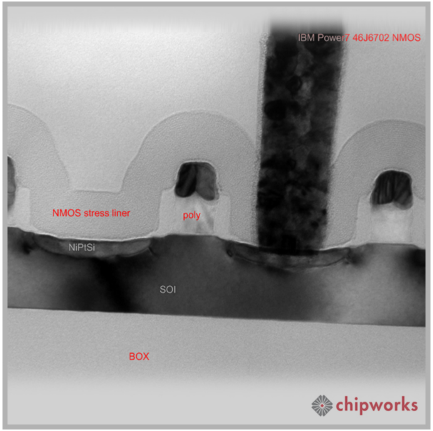
PPC970fx (90nm)

MOS Transistor : 2008



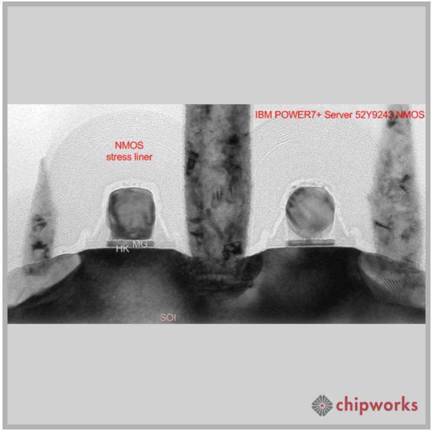
Power6 (65nm)

MOS Transistor : 2011



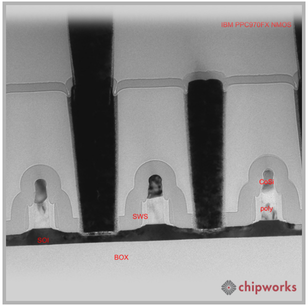
Power7 (45nm)

MOS Transistor : 2013

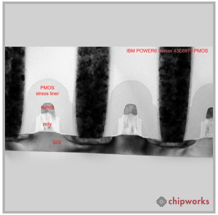


Power7+ (32nm)

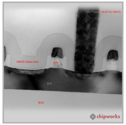
Using the same scale



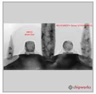
2004
90nm
PPC970fx



2009
65nm
Power6



2011
45nm
Power7



2013
32 nm
Power7+

Photo Credits

The images are from the analysis of the evolution of IBM technologies made by Chipworks Inc.
The analysis as well as the original images were available in 2014 here :
`http://www.chipworks.com/en/technical-competitive-analysis/resources/blog/ibm-continues-major-source-chip-innovation/`

Practical downsizing

What are today problems ?

- For CPU, frequencies have reached their maximal values (from 3 to 4 GHz) at the beginning of the century. This is due to the maximum heat dissipation of the chips.
- When lowering the power-supply voltage we can no longer reach the "ideal switch" approximation : chips have larger and larger static dissipation added to the computation dissipation.
- Technologists must use more and more complex (costly) manufacturing processes to continue to follow the "Moore's Law"..
- At the end of the previous century, some predicted the end for "Moore's law" for scientific reasons (MOS transistor physics), it seems, since 2014, that the main difficulty is economical.

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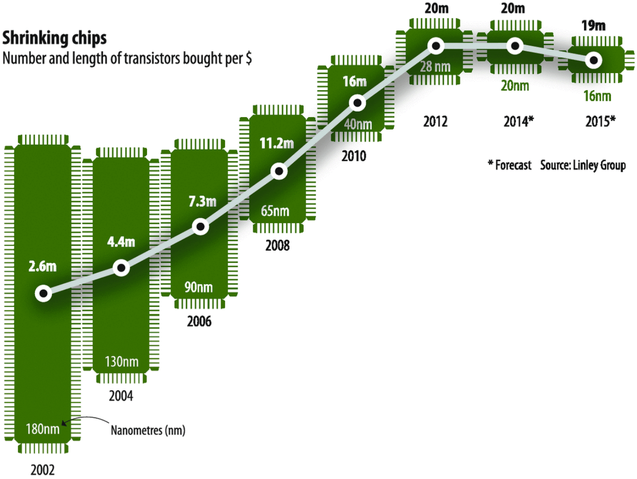
Technology downsizing

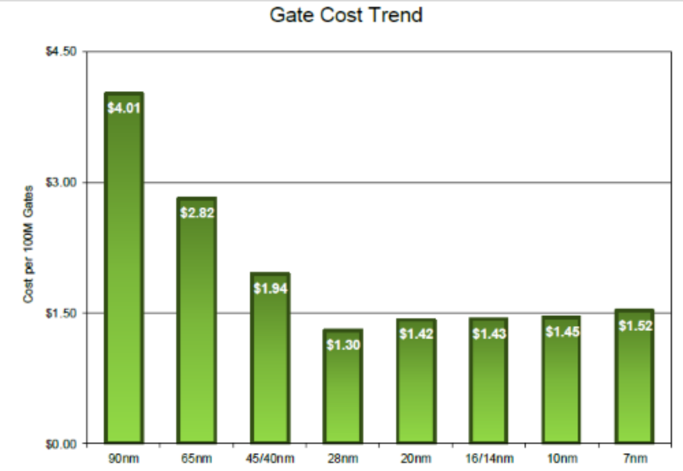
(forecast 2013) The end of Moore's law ?



* Forecast Source: Linley Group

Technology downsizing

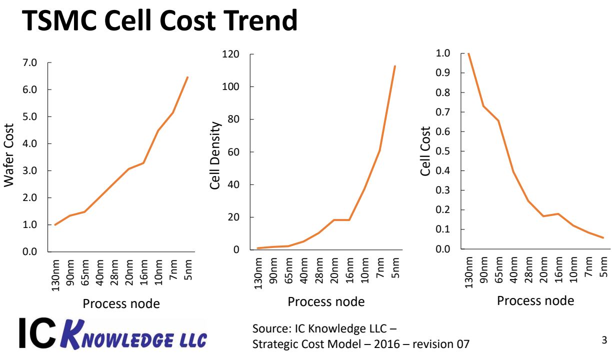
(forecast 2016) Controversy continues



Source: International Business Strategies, Inc.

Technology downsizing

(2016) TSMC technologies

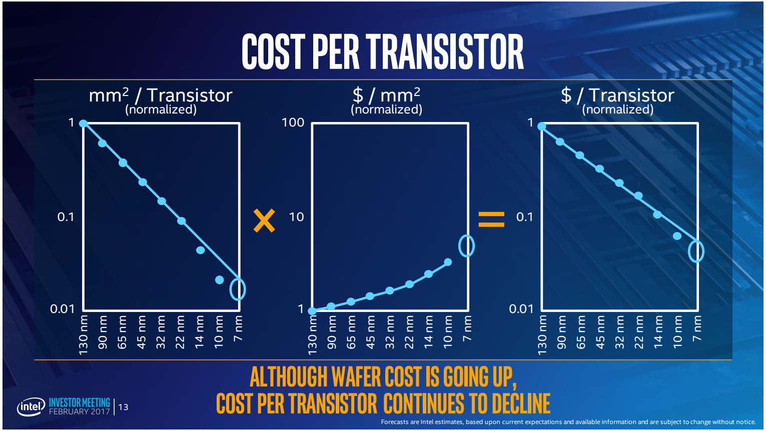


TSMC Cell Cost Trend

Source: IC Knowledge LLC –
Strategic Cost Model – 2016 – revision 07

Technology downsizing

(2017) Intel Investor Meeting



COST PER TRANSISTOR

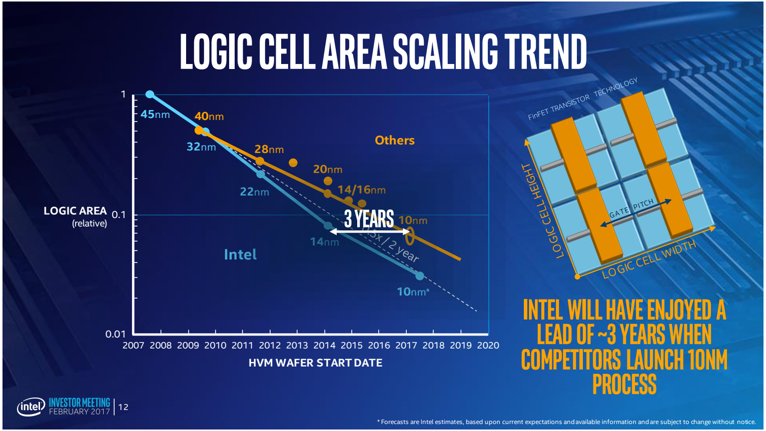
ALTHOUGH WAFER COST IS GOING UP,
COST PER TRANSISTOR CONTINUES TO DECLINE

intel INVESTOR MEETING FEBRUARY 2017 | 13

Forecasts are Intel estimates, based upon current expectations and available information and are subject to change without notice.

Technology downsizing

(2017) Gate length is no longer a good metric



LOGIC CELL AREA SCALING TREND

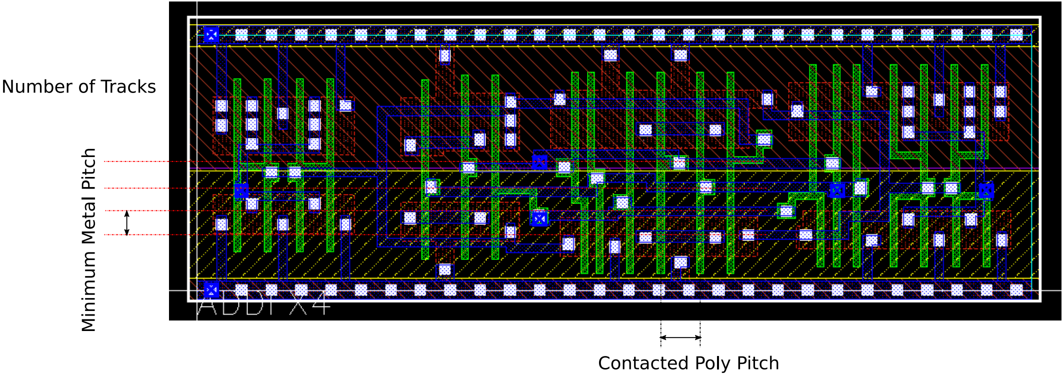
INTEL WILL HAVE ENJOYED A LEAD OF ~3 YEARS WHEN COMPETITORS LAUNCH 10NM PROCESS

* Forecasts are Intel estimates, based upon current expectations and available information and are subject to change without notice.

Technology downsizing

Concept of "Standard node"

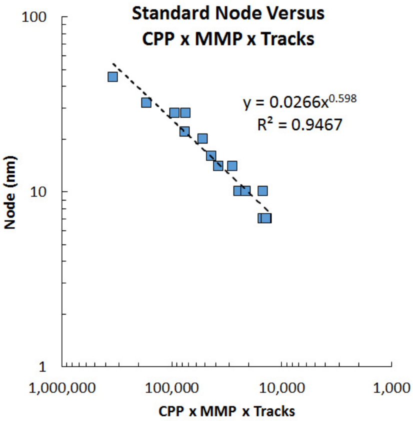
- $Cell\_area \propto CPP * MMP * Tracks$



Technology downsizing

"Standard Node Versus area formula"

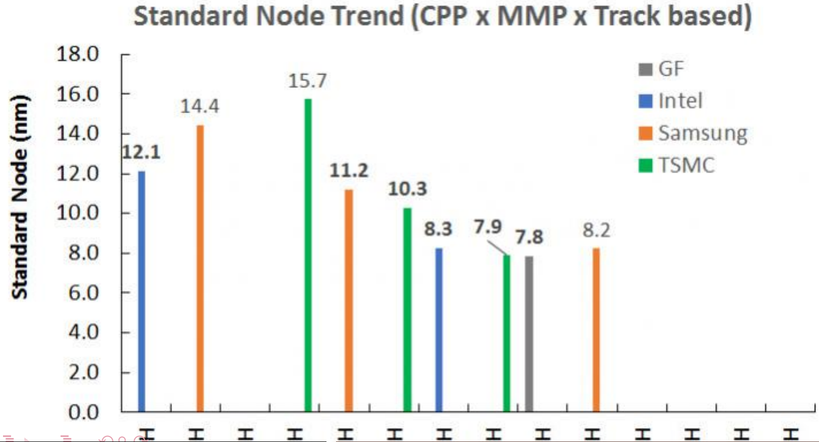
- source :https ://www.semiwiki.com
- 54 processes from 12 companies

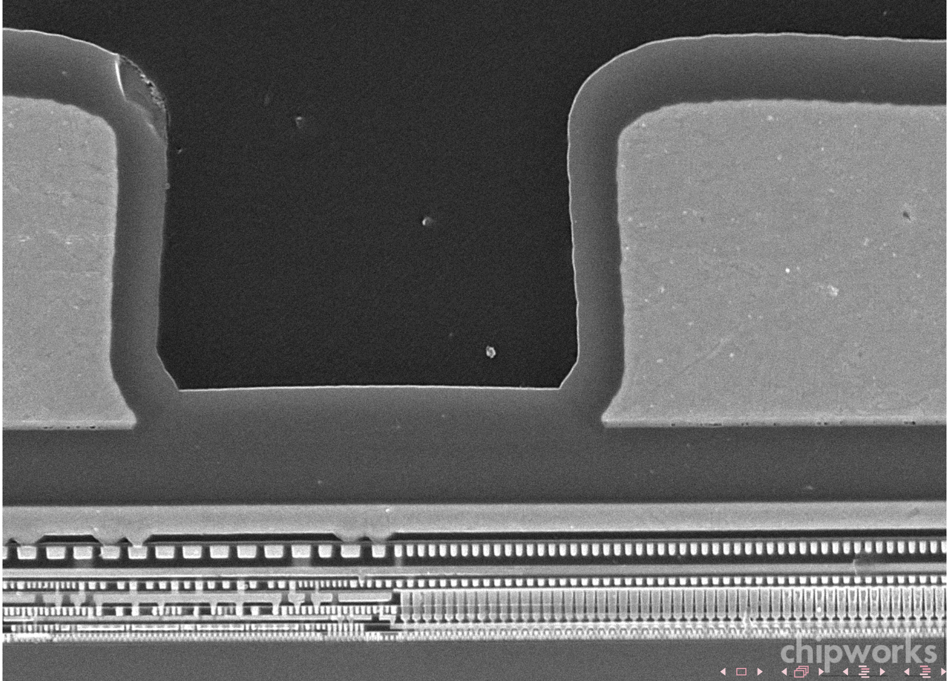


Technology downsizing

"Standard Node By Company"

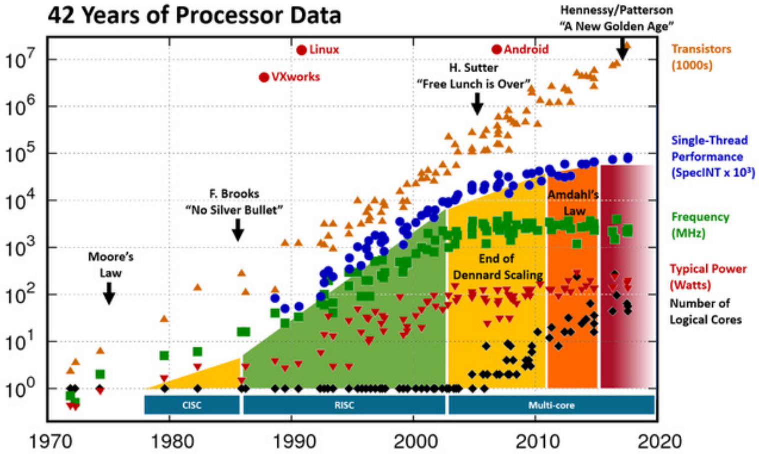
- source :https ://www.semiwiki.com
- Annoucements : Intel(14nm, 10nm) Tsmc(16nm, 10nm, 7nm)





chipworks

Performance evolution



Hennessy and Patterson, Turing Lecture 2018, overlaid over "42 Years of Processors Data"
https://www.karlrupp.net/2018/02/42-years-of-microprocessor-trend-data/
Original data up to the year 2010 collected and plotted by M. Horowitz, F. Labonte, O. Shacham, K. Olukotun, L. Hammond, and C. Batten
New plot and data collected for 2010-2017 by K. Rupp

Gordon Moore Fishing

source https://commons.wikimedia.org/wiki/File:Gordon_moore_fishing.jpg